

# RJE0629JSP

Silicon P Channel MOS FET Series  
Power Switching

R07DS1564EJ0100  
Rev.1.00  
Jun 12, 2024

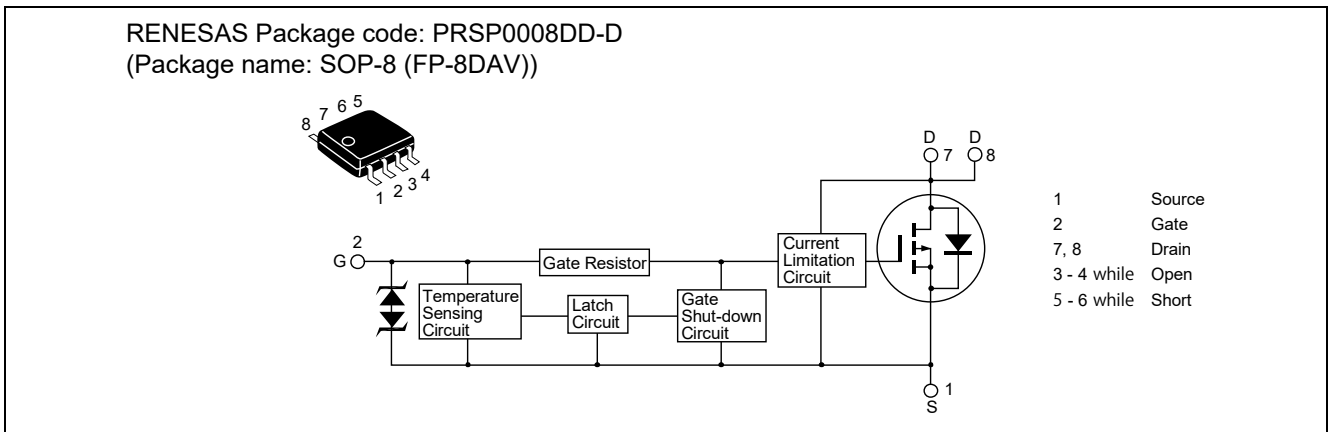
## Description

This FET has the over temperature shut-down capability sensing to the junction temperature. This FET has the built-in over temperature shut-down circuit in the gate area. And this circuit operation to shut-down the gate voltage in case of high junction temperature like applying over power consumption, over current etc..

## Features

- High endurance capability against to the short circuit.
- Built-in the over temperature shut-down circuit.
- Latch type shut down operation (need 0 voltage recovery).
- Built-in the current limitation circuit.
- Low on-resistance  $R_{DS(on)}$  : 140 mΩ Typ, 260 mΩ Max ( $V_{GS} = -10$  V)
- Power supply voltage applies 12 V.
- AEC-Q101 Rev-C compliant.

## Outline



## Absolute Maximum Ratings

( $T_a = 25^\circ\text{C}$ )

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSS}$	-60	V
Gate to source voltage	$V_{GSS}$	-16	V
Gate to source voltage	$V_{GSS}$	2.5	V
Drain current	$I_D$ Note3	-1.5	A
Body-drain diode reverse drain current	$I_{DR}$	-1.5	A
Avalanche current	$I_{AP}$ Note 2	-1.5	A
Avalanche energy	$E_{AR}$ Note 2	9.6	mJ
Channel dissipation	$P_{ch}$ Note 1	2	W
Channel temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

- Notes: 1. When using the glass epoxy board (FR4 40 × 40 × 1.6 mm),  $PW \leq 10$  s  
 2.  $T_{ch} = 25^\circ\text{C}$ ,  $R_g \geq 50 \Omega$   
 3. It provides by the current limitation lower bound value.

## Typical Operation Characteristics

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Input voltage	V <sub>IH</sub>	-3.5	—	—	V	
	V <sub>IL</sub>	—	—	-1.2	V	
Input current (Gate non shut down)	I <sub>IH1</sub>	—	—	-100	μA	V <sub>i</sub> = -8 V, V <sub>DS</sub> = 0
	I <sub>IH2</sub>	—	—	-50	μA	V <sub>i</sub> = -3.5 V, V <sub>DS</sub> = 0
	I <sub>IL</sub>	—	—	-10	μA	V <sub>i</sub> = -1.2 V, V <sub>DS</sub> = 0
Input current (Gate shut down)	I <sub>IH(sd)1</sub>	—	-0.8	—	mA	V <sub>i</sub> = -8 V, V <sub>DS</sub> = 0
	I <sub>IH(sd)2</sub>	—	-0.35	—	mA	V <sub>i</sub> = -3.5 V, V <sub>DS</sub> = 0
Shut down temperature	T <sub>sd</sub>	—	175	—	°C	Channel temperature (dv/dt V <sub>GS</sub> ≥ 500 V/ms)
Gate operation voltage	V <sub>op</sub>	-3.5	—	-12	V	
Drain current (Current limitation value)	I <sub>D limit</sub>	-1.5	—	—	A	V <sub>GS</sub> = -12 V, V <sub>DS</sub> = -10 V <sup>Note 4</sup>

Notes; 4. Pulse test

## Electrical Characteristics

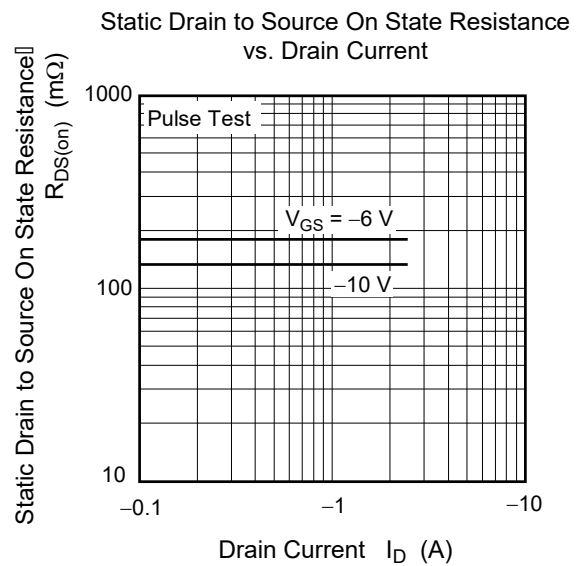
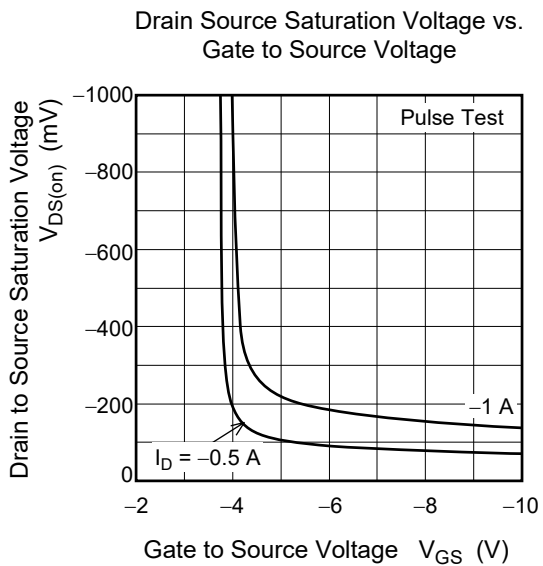
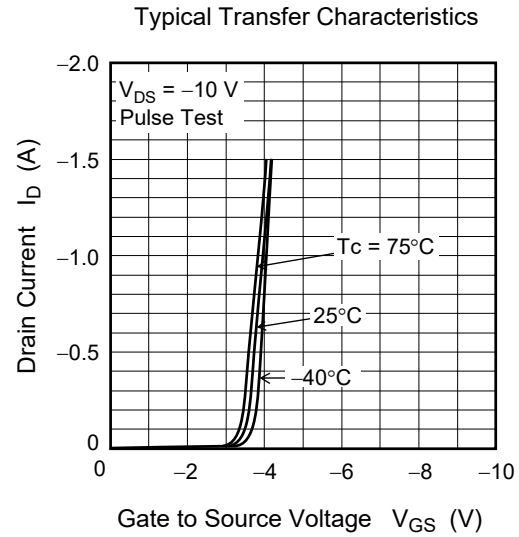
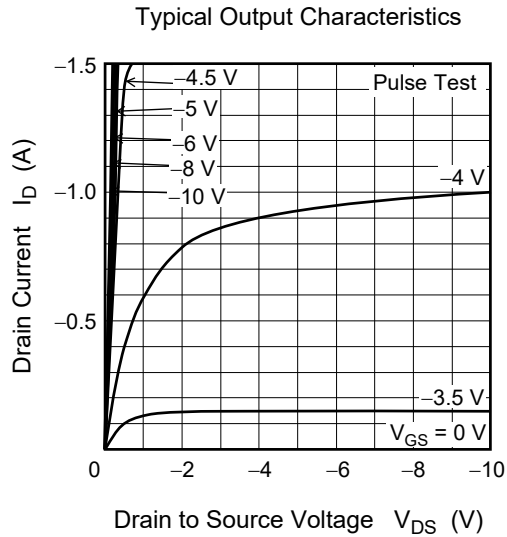
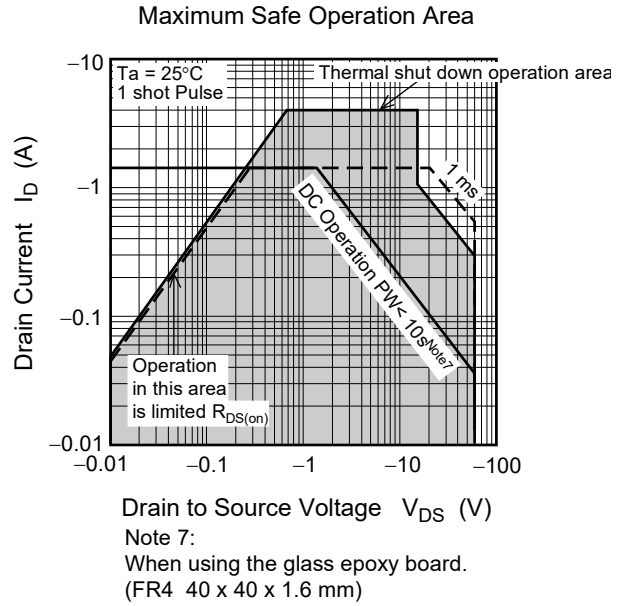
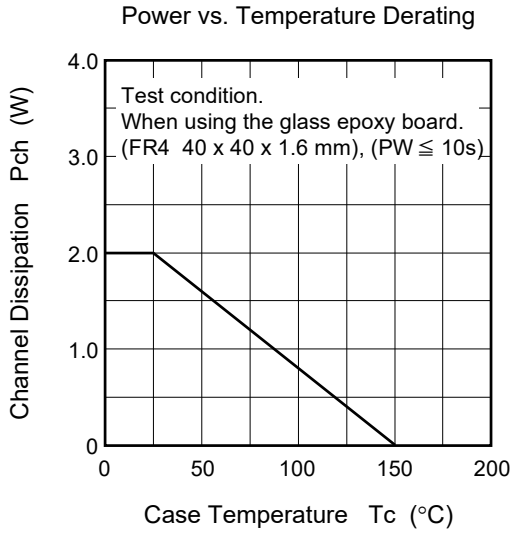
(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain current	I <sub>D1</sub>	—	—	-2	A	V <sub>GS</sub> = -3.5 V, V <sub>DS</sub> = -10 V
	I <sub>D2</sub>	—	—	-10	mA	V <sub>GS</sub> = -1.2 V, V <sub>DS</sub> = -10 V
	I <sub>D3</sub>	-1.5	—	—	A	V <sub>GS</sub> = -12 V, V <sub>DS</sub> = -10 V <sup>Note 5</sup>
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	-60	—	—	V	I <sub>D</sub> = -10 mA, V <sub>GS</sub> = 0
Gate to source breakdown voltage	V <sub>(BR)GSS1</sub>	-16	—	—	V	I <sub>G</sub> = -800 μA, V <sub>DS</sub> = 0
	V <sub>(BR)GSS2</sub>	2.5	—	—	V	I <sub>G</sub> = 100 μA, V <sub>DS</sub> = 0
Gate to source leak current	I <sub>GSS1</sub>	—	—	-100	μA	V <sub>GS</sub> = -8 V, V <sub>DS</sub> = 0
	I <sub>GSS2</sub>	—	—	-50	μA	V <sub>GS</sub> = -3.5 V, V <sub>DS</sub> = 0
	I <sub>GSS3</sub>	—	—	-10	μA	V <sub>GS</sub> = -1.2 V, V <sub>DS</sub> = 0
	I <sub>GSS4</sub>	—	—	100	μA	V <sub>GS</sub> = 2.4 V, V <sub>DS</sub> = 0
Input current (shut down)	I <sub>GS(OP)1</sub>	—	-0.8	—	mA	V <sub>GS</sub> = -8 V, V <sub>DS</sub> = 0
	I <sub>GS(OP)2</sub>	—	-0.35	—	mA	V <sub>GS</sub> = -3.5 V, V <sub>DS</sub> = 0
Zero gate voltage drain current	I <sub>DSS1</sub>	—	—	-10	μA	V <sub>DS</sub> = -60 V, V <sub>GS</sub> = 0
	I <sub>DSS2</sub>	—	—	-10	μA	V <sub>DS</sub> = -48 V, V <sub>GS</sub> = 0 Ta = 125°C
Gate to source cutoff voltage	V <sub>GS(off)</sub>	-2.2	—	-3.4	V	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -1 mA
Static drain to source on state resistance	R <sub>DS(on)1</sub>	—	185	380	mΩ	I <sub>D</sub> = -0.75 A, V <sub>GS</sub> = -6 V <sup>Note 5</sup>
	R <sub>DS(on)2</sub>	—	140	260	mΩ	I <sub>D</sub> = -0.75 A, V <sub>GS</sub> = -10 V <sup>Note 5</sup>
Output capacitance	C <sub>oss</sub>	—	194	—	pF	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0, f = 1MHz
Turn-on delay time	t <sub>d(on)</sub>	—	1.82	—	μs	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -0.75 A, R <sub>L</sub> = 40 Ω
Rise time	t <sub>r</sub>	—	1.95	—	μs	
Turn-off delay time	t <sub>d(off)</sub>	—	0.99	—	μs	
Fall time	t <sub>f</sub>	—	0.84	—	μs	
Body-drain diode forward voltage	V <sub>DF</sub>	—	0.83	—	V	I <sub>F</sub> = -1.5 A, V <sub>GS</sub> = 0
Body-drain diode reverse recovery time	t <sub>rr</sub>	—	85	—	ns	I <sub>F</sub> = -1.5 A, V <sub>GS</sub> = 0 di <sub>F</sub> /dt = 50 A/μs
Over load shut down operation time <sup>Note 6</sup>	t <sub>os1</sub>	—	18.6	—	ms	V <sub>GS</sub> = -5 V, V <sub>DD</sub> = -16 V

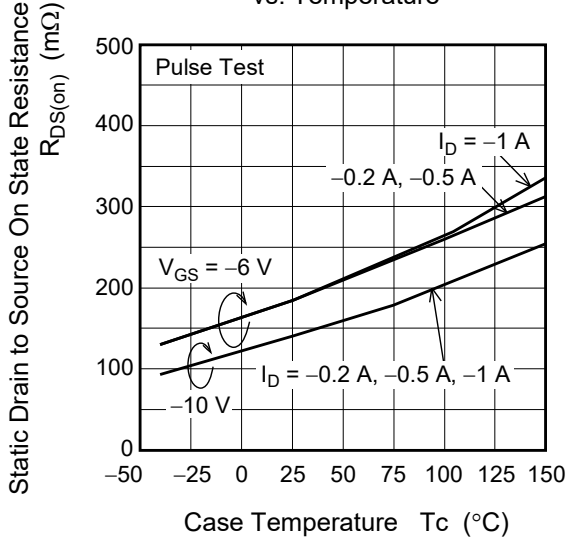
Notes: 5. Pulse test

6. Including the junction temperature rise of the over loaded condition.

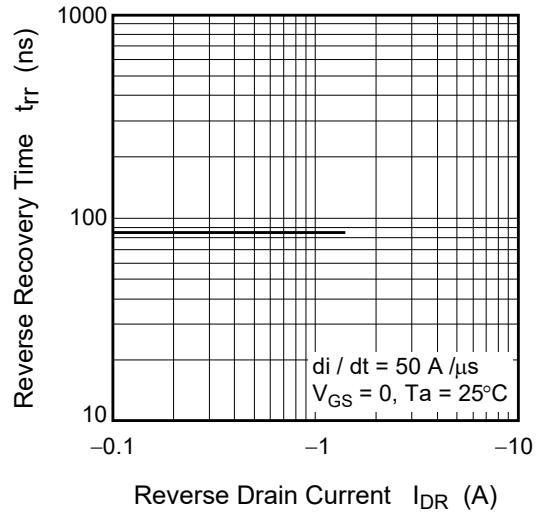
### Main Characteristics



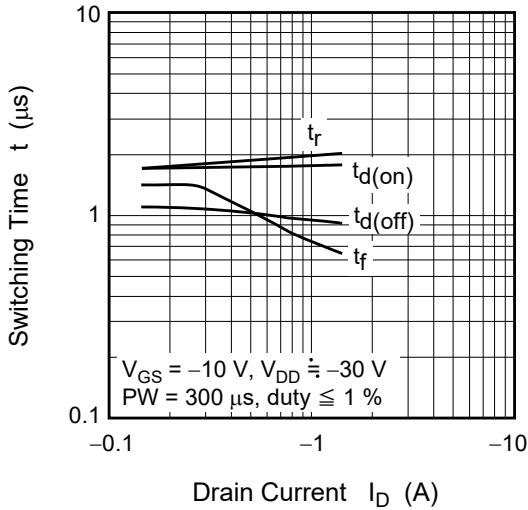
Static Drain to Source On State Resistance vs. Temperature



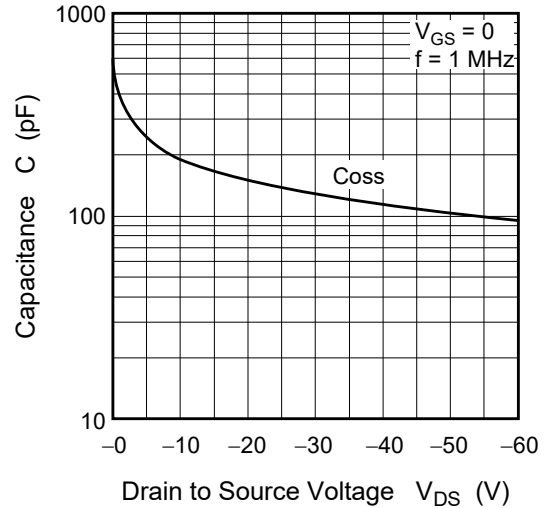
Body-Drain Diode Reverse Recovery Time



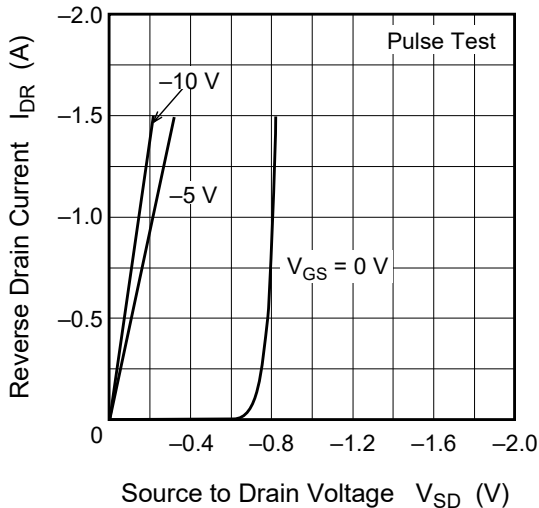
Switching Characteristics



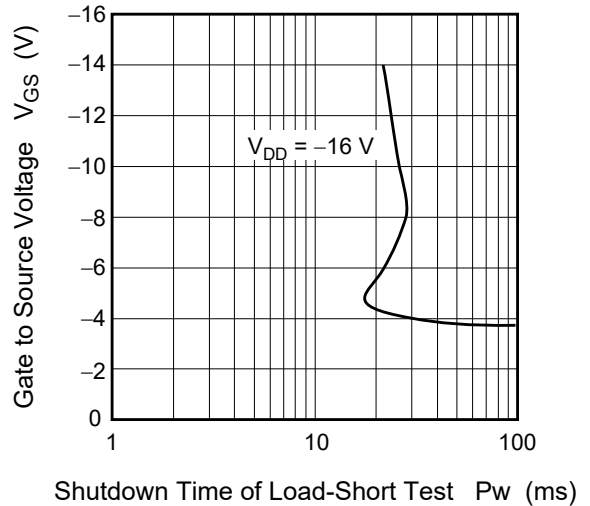
Typical Capacitance vs. Drain to Source Voltage



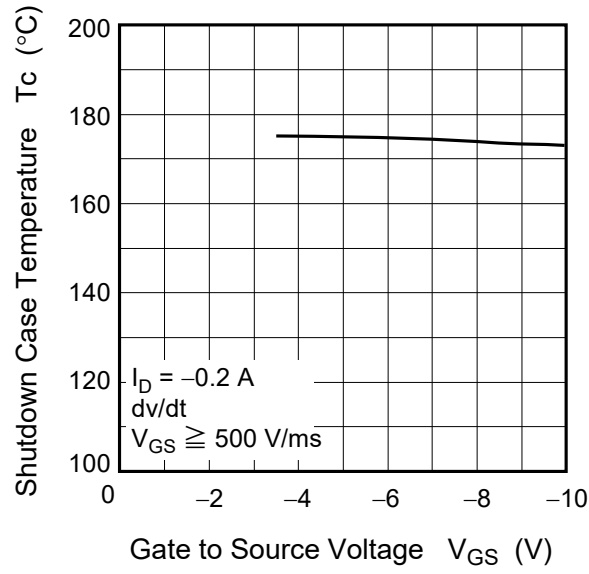
Reverse Drain Current vs. Source to Drain Voltage



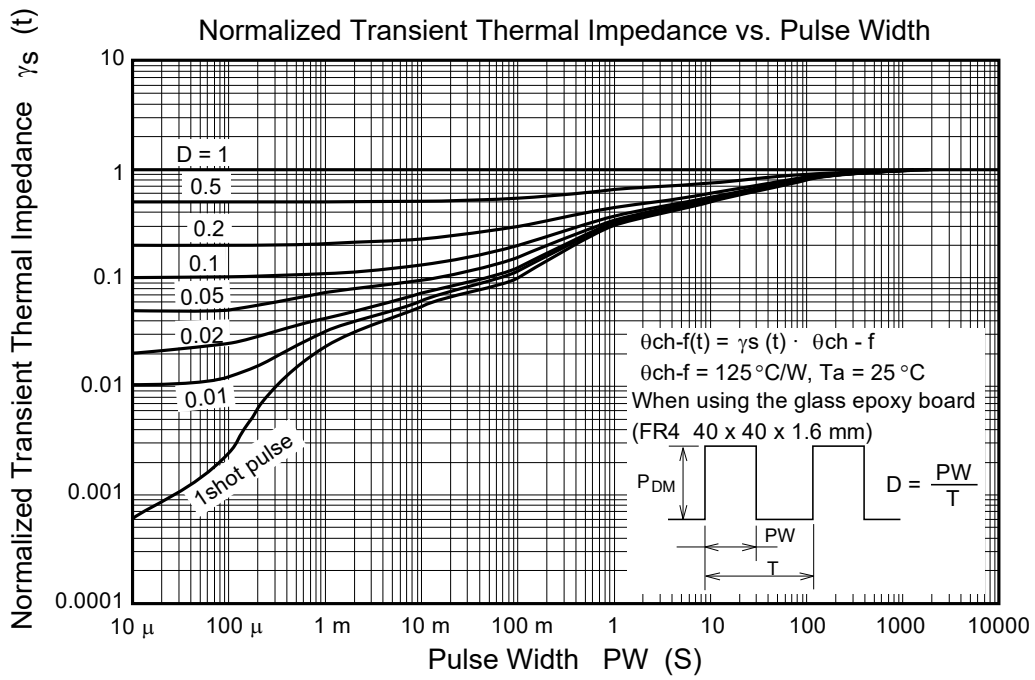
Gate to Source Voltage vs. Shutdown Time of Load-Short Test

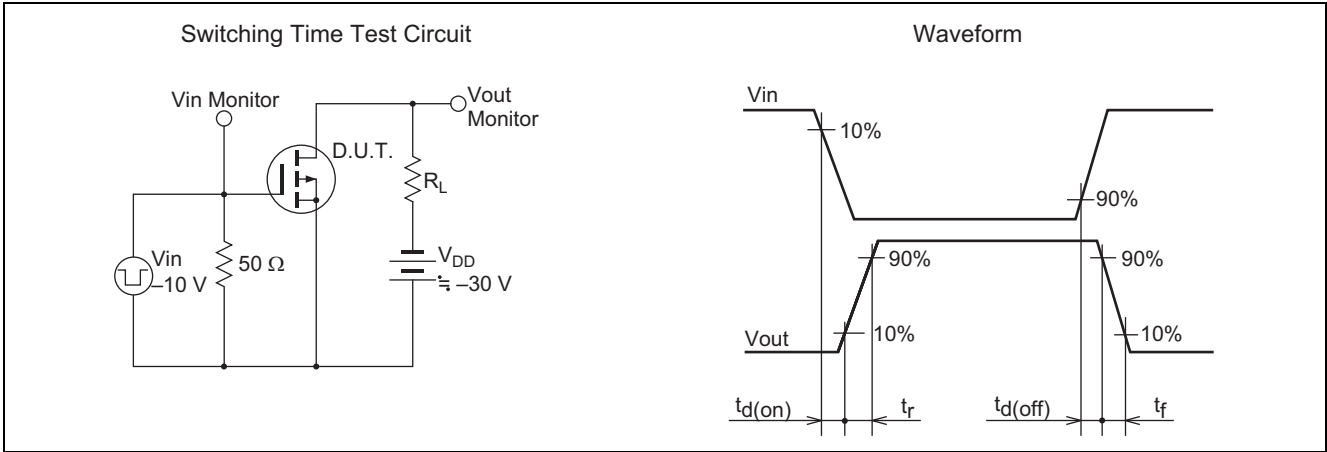


Shutdown Case Temperature vs. Gate to Source Voltage

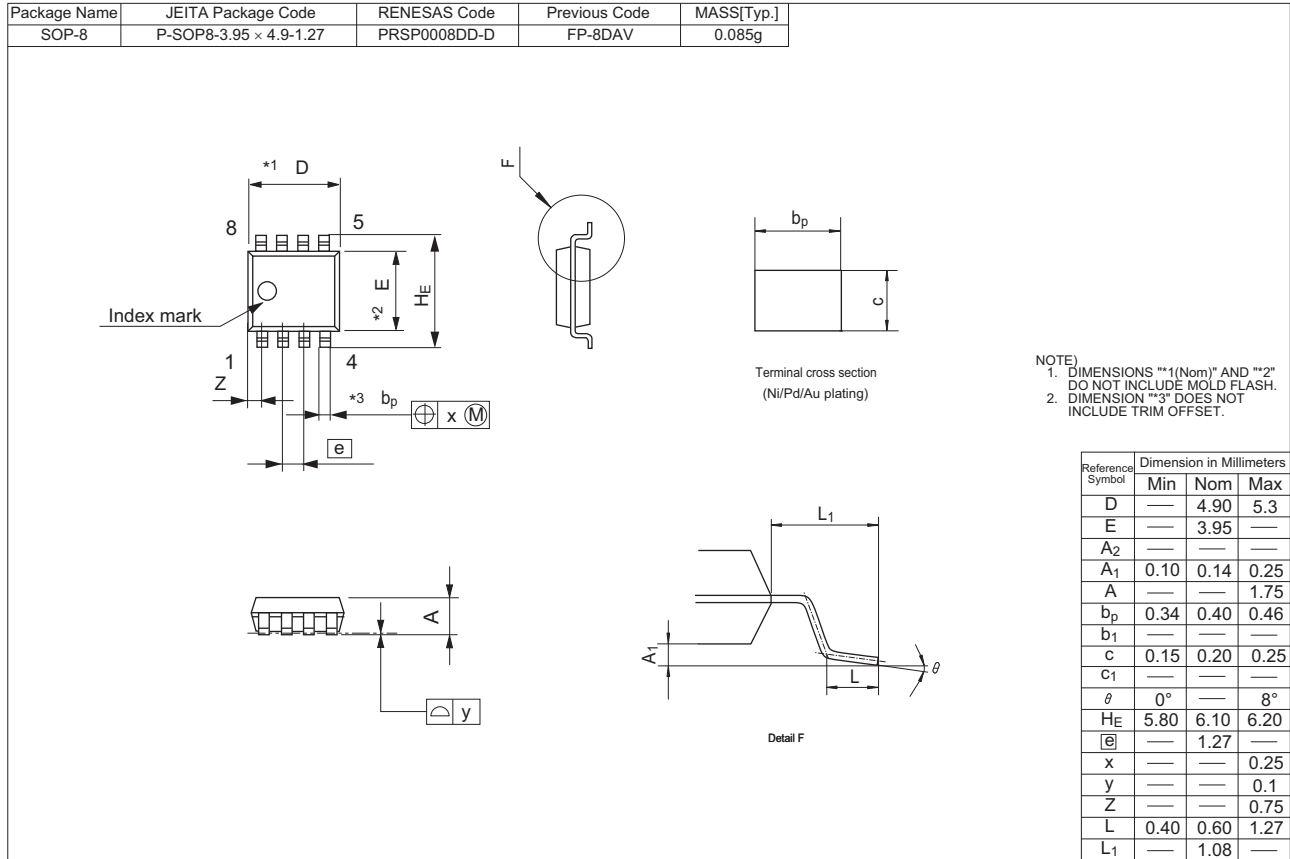


Normalized Transient Thermal Impedance vs. Pulse Width





### Package Dimensions



### Ordering Information

Part No.	Quantity	Shipping Container
RJE0629JSP-00-J0	2500 pcs/reel	Taping

Note: The symbol of 2nd "-" is occasionally presented as "#".

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(Rev.5.0-1 October 2020)

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